

	No.2746	2SK1065
		N-Channel Junction Silicon FET High-Frequency General-Purpose Amp Applications

Features

- Very small-sized package permitting 2SK1065-applied sets to be made smaller and slimmer
- Small c_{rss} ($c_{rss} = 0.04\text{pF}$ typ)

Absolute Maximum Ratings at $T_a = 25^\circ\text{C}$

			unit
Gate to Drain Voltage	V_{GDO}	-20	V
Gate Current	I_G	10	mA
Drain Current	I_D	20	mA
Allowable Power Dissipation	P_D	150	mW
Junction Temperature	T_j	150	$^\circ\text{C}$
Storage Temperature	T_{stg}	-55 to +150	$^\circ\text{C}$

Electrical Characteristics at $T_a = 25^\circ\text{C}$

			min	typ	max	unit
Gate to Drain Breakdown Voltage	$V_{(BR)GDO}$	$I_G = -10\mu\text{A}$	-20			V
Gate Cutoff Current	I_{GSS}	$V_{GS} = -0.5\text{V}, V_{DS} = 0$			-10	nA
Cutoff Voltage	$V_{GS(off)}$	$V_{DS} = 5\text{V}, I_D = 10\mu\text{A}$	-0.4	-1.3	-2.5	V
Drain Current	I_{DSS}	$V_{DS} = 5\text{V}, V_{GS} = 0$	$\times 1.2$		$\times 12.0$	mA
Forward Transfer Admittance	$ y_{fs} (1)$	$V_{DS} = 5\text{V}, V_{GS} = 0, f = 1\text{kHz}$	2.4	6.0		mS
	$ y_{fs} (2)$	$V_{DS} = 5\text{V}, V_{GS} = 0, f = 100\text{MHz}$	2.4	6.0		mS
Input Capacitance	c_{iss}	$V_{DS} = 5\text{V}, V_{GS} = 0, f = 1\text{MHz}$		4.0		pF
Reverse Transfer Capacitance	c_{rss}	$V_{DS} = 5\text{V}, V_{GS} = 0, f = 1\text{MHz}$		0.04	0.15	pF
Output Capacitance	c_{oss}	$V_{DS} = 5\text{V}, V_{GS} = 0, f = 1\text{MHz}$		4.0		pF
Power Gain	PG	$V_{DS} = 5\text{V}, V_{GS} = 0, f = 100\text{MHz}$		24		dB
Noise Figure	NF	See specified Test Circuit.		3.5	6.0	dB

※: The 2SK1065 is classified by I_{DSS} as follows (unit: mA):

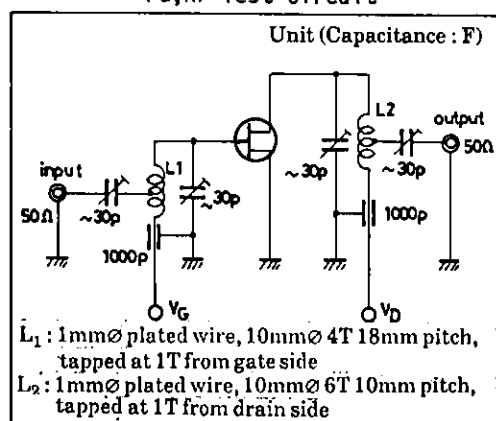
1.2	3	3.0	2.5	4	6.0	5.0	5	12.0
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(Note) Marking: T

I_{DSS} rank: 3, 4, 5

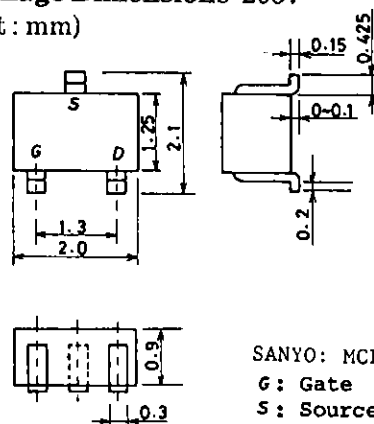
• For CP package version, use the 2SK242.

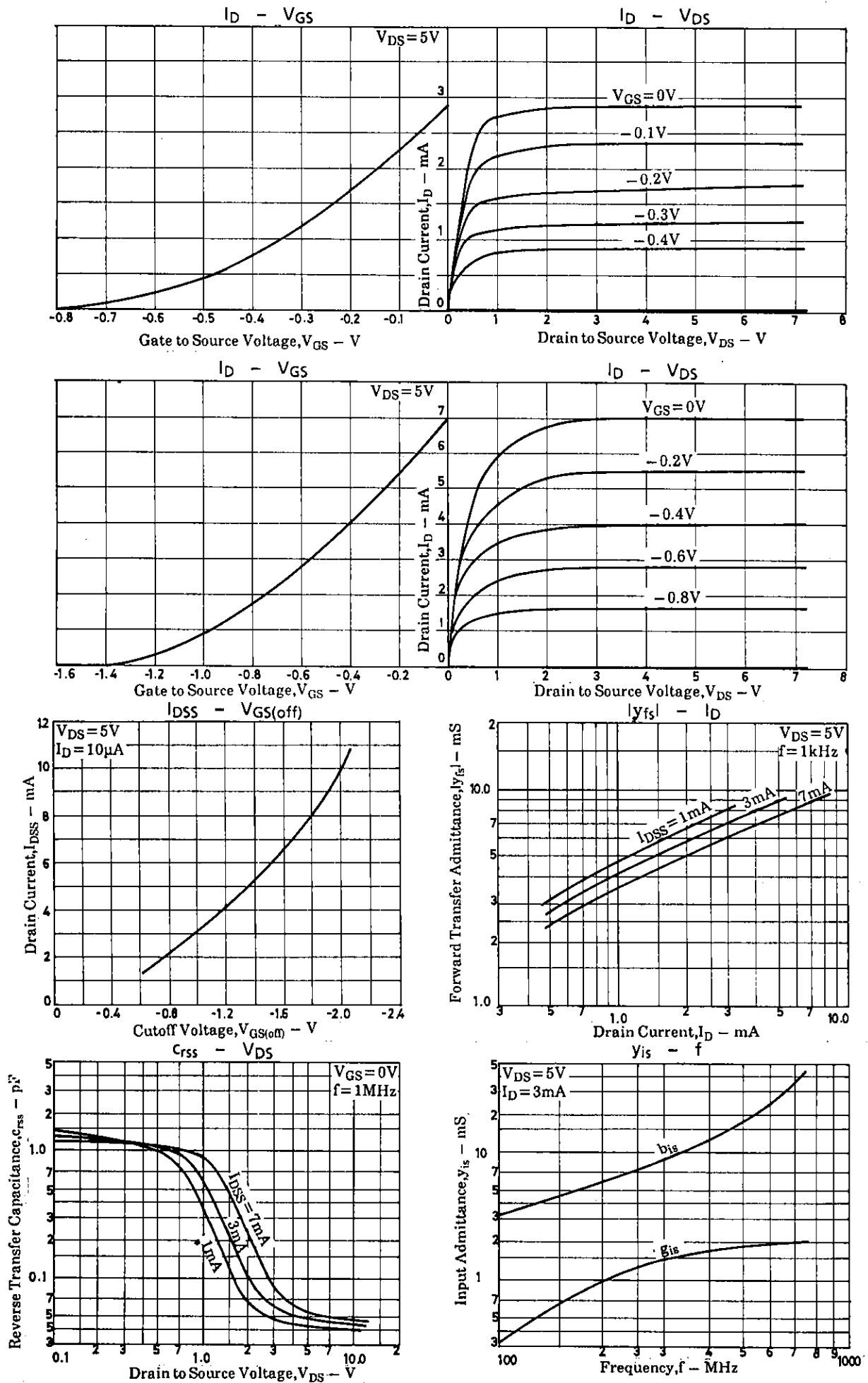
PG, NF Test Circuit

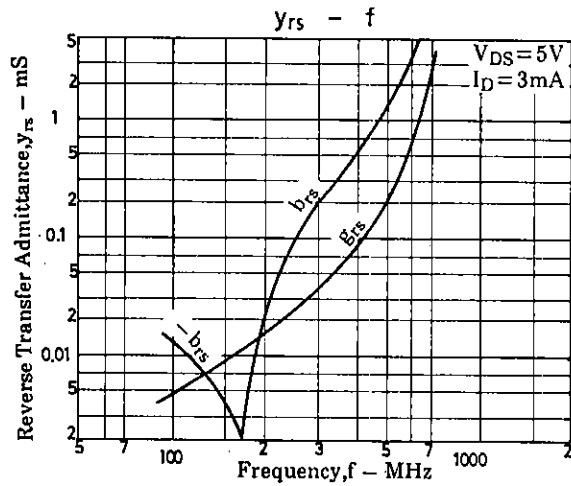
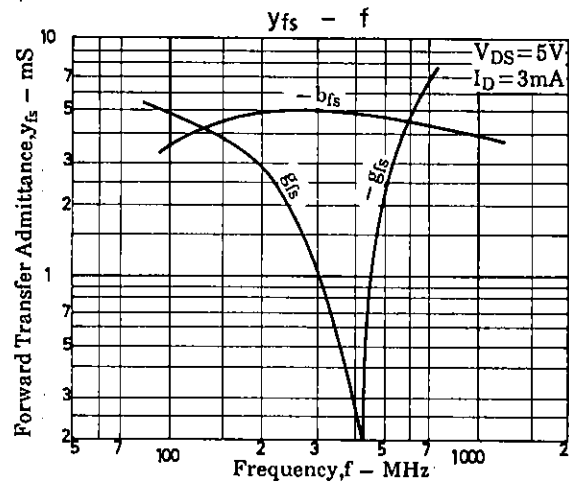
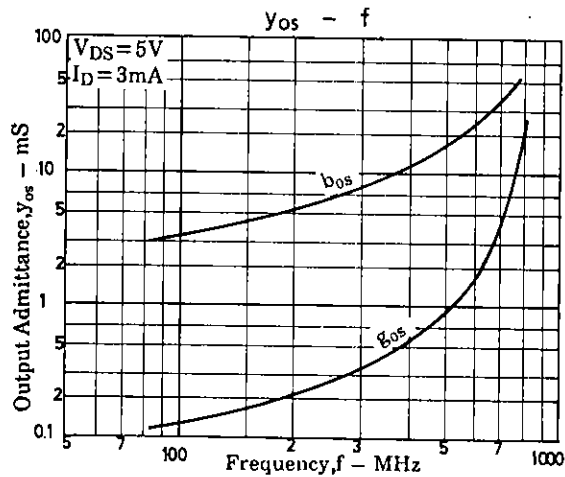
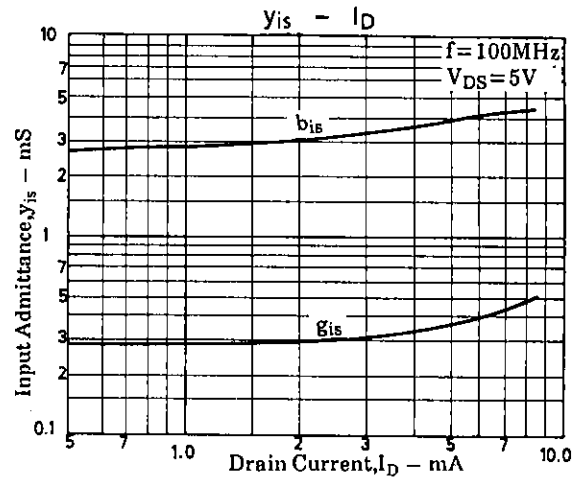
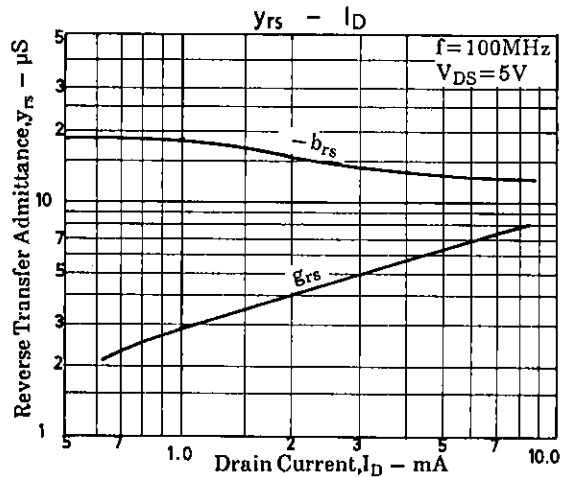
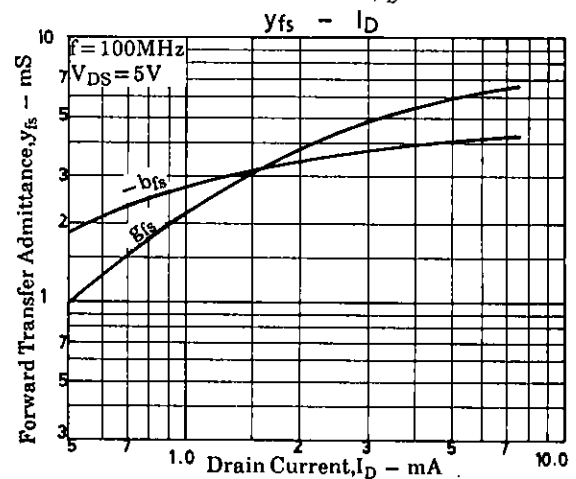
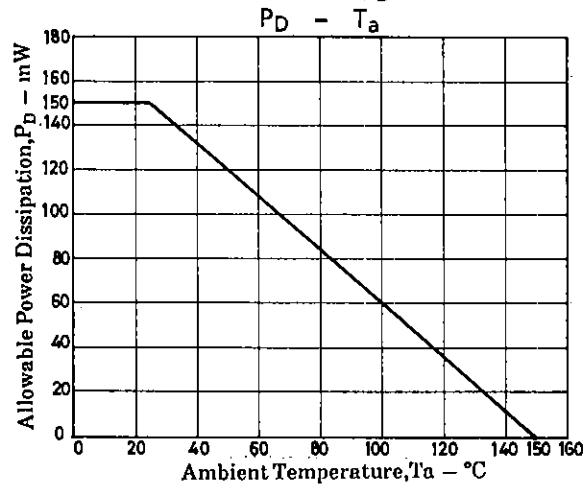


Package Dimensions 2057

(unit: mm)







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